AMENDMENTS TO THE SPECIFICATION:

Please replace the title with the following amended title:

SEMICONDUCTOR LASER DEVICE WITH A ROUNDED BASE MESA STRUCTURE

Kindly replace the paragraph bridging pages 7 and 8 with the following amended paragraph:

The upper material layer 140~~, which is the characteristic of the present invention,~~ includes an upper cladding layer 141 and a second compound semiconductor layer 142. The upper cladding layer 141 is stacked on the upper surface of the upper wave guide layer 133 and has a protruded current injection ridge 141a at its center and protruded force distribution ridges 141b adjacent to the current injection ridge 141a. The second compound semiconductor layer 142 acts as an ohmic contact layer and is stacked on the current injection ridge 141a. When the lower cladding layer 122 is an n-type compound semiconductor layer, the upper cladding layer 141 is a p-type compound semiconductor layer. When the lower cladding layer 122 is a p-type compound semiconductor layer, the upper cladding layer 141 is an n-type compound semiconductor layer. In other words, when the lower cladding layer 122 is the n-GaN/AlGaN layer, the upper cladding layer 141 is a p-GaN/AlGaN layer. Similarly, when the first compound semiconductor layer 121 is an n-type compound semiconductor layer, the second compound semiconductor layer 142 is a p-type compound semiconductor layer, and when the first compound semiconductor layer 121 is formed of n-GaN, the second compound semiconductor layer 142 is formed of p-GaN. A passivation layer 151 is formed on the ridges 141a

and 141b. The passivation layer 151 includes a contact hole 151a that exposes the current injection ridge 141a, and a p-type upper electrode 152 is formed therein.